Features

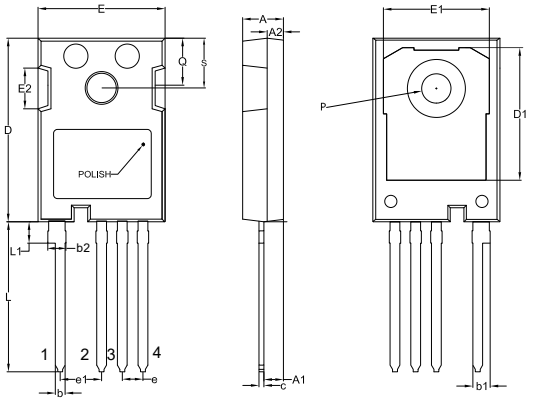
- High Speed Smooth Switching Device for Hard & Soft Switching
- Positive Temperature Coefficient
- High Ruggedness ,Temperature Stable
- Maximum junction temperature 175℃
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant (Note 2)("P" Suffix Designates RoHS Compliant. See Ordering Information)

Applications

- Solar converters
- Uninterruptible power supplies
- Mid to high range switching frequency converters
- Welding Converters

Trench and Field Stop IGBT 650V 75A

TO-247-4



Maximum Ratings

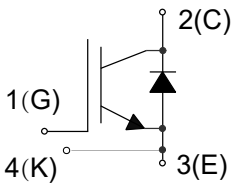
Parameter		Symbol	Rating	Unit
Collector-Emitter Voltage		V_{CE}	650	V
DC Collector Current (Note 3)	T_C=25°C	I_C	85 (Note 4)	A
	T_C=100°C		80	
Pulsed Collector Current, V_{GE}=15V (Note 5)		$I_{C,pluse}$	300	A
Diode Forward Current (Note 3)	T_C=25°C	I_F	85 (Note 4)	A
	T_C=100°C		80	
Diode Pulsed Current (Note 5)		$I_{F,pluse}$	300	A
Gate-Emitter Voltage		V_{GE}	±20	V
Transient Gate-Emitter Voltage (Note 6)			±30	
Power Dissipation	T_C=25°C	P_D	428	W
	T_C=100°C		214	

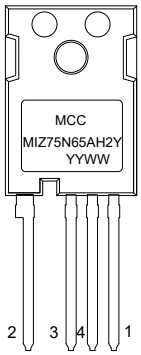
Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.
3. Limited by T_{Jmax}.
4. Value limited by bondwire.
5. T_p limited by T_{Jmax}.
6. T_p≤10us, Duty Cycle<1%.

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.090	0.098	2.29	2.50	
A2	0.074	0.082	1.88	2.08	
b	0.043	0.054	1.10	1.36	
b1	0.093	0.108	2.35	2.75	
b2	0.094	0.112	2.39	2.84	
c	0.022	0.028	0.55	0.70	
D	0.917	0.929	23.30	23.60	
D1	0.640	0.663	16.25	16.85	
E	0.620	0.632	15.75	16.05	
E1	0.543	0.559	13.80	14.20	
E2	0.173	0.201	4.4	5.10	
e	0.100		2.54		
e1	0.199		5.06		
L	0.683	0.694	17.34	17.64	
L1	0.157	0.169	4.00	4.30	
P	0.138	0.148	3.51	3.75	Φ
Q	0.220	0.236	5.60	6.00	
S	0.220	0.248	5.60	6.30	

Internal Structure





Device Code: MIZ75N65AH2Y

Date Code: YYWW (Year & Week)

Electrical Characteristics of the IGBT @ T_J=25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
IGBT Static Characteristics						
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=250μA	650			V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=75A, T_J=25℃	1.20	1.65	2.10	V
		V_{GE}=15V, I_C=75A, T_J=125℃		1.95		
		V_{GE}=15V, I_C=75A, T_J=150℃		2.05		
G-E Threshold Voltage	$V_{GE(th)}$	I_C=0.75mA, V_{CE}=V_{GE}	3.2	4.0	4.8	V
C-E Leakage Current	I_{CES}	V_{CE}=650V, V_{GE}=0V, T_J=25℃			0.25	mA
		V_{CE}=650V, V_{GE}=0V, T_J=150°C			3.00	
G-E Leakage Current	I_{GES}	V_{CE}=0V, V_{GE}=±20V			100	nA
Dynamic Characteristics						
Input Capacitance	C_{ies}	V_{CE}=25V,V_{GE}=0V,f=1MHz		4.59		nF
Reverse Transfer Capacitance	C_{res}			0.03		
Gate Charge	Q_g	V_{CC}=520V,I_C=75A,V_{GE}=15V		0.17		μC
IGBT Switching Characteristics						
Turn-On Delay Time	$td_{(on)}$	V_{CC}=400V, I_C=75A, V_{GE}=-5V~15V, R_G=10Ω,T_J=25°C Inductive Load		30		ns
Rise Time	t_r			95		
Turn-Off Delay Time	$td_{(off)}$			142		
Fall Time	t_f			41		
Turn-On Energy	E_{on}			2.61		mJ
Turn-Off Energy	E_{off}			0.76		
Turn-On Delay Time	$td_{(on)}$	V_{CC}=400V, I_C=75A, V_{GE}=-5V~15V, R_G=10Ω,T_J=125°C Inductive Load		27		ns
Rise Time	t_r			88		
Turn-Off Delay Time	$td_{(off)}$			151		
Fall Time	t_f			50		
Turn-On Energy	E_{on}			2.71		mJ
Turn-Off Energy	E_{off}			0.88		
Turn-On Delay Time	$td_{(on)}$	V_{CC}=400V, I_C=75A, V_{GE}=-5V~15V, R_G=10Ω,T_J=150°C Inductive Load		25		ns
Rise Time	t_r			84		
Turn-Off Delay Time	$td_{(off)}$			159		
Fall Time	t_f			55		
Turn-On Energy	E_{on}			2.78		mJ
Turn-Off Energy	E_{off}			0.97		

Electrical Characteristics of the Diode @ T_J=25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Diode Characteristics						
Diode Forward Voltage	V_F	V_{GE}=0V, I_F=75A, T_J=25℃		1.75	2.20	V
		V_{GE}=0V, I_F=75A, T_J=125℃		1.65		
		V_{GE}=0V, I_F=75A, T_J=150℃		1.60		
Reverse Recovery Current	I_{rr}	V_R=400V, I_F=75A, di_F/dt=-440A/μs, T_J=25°C		10		A
Diode Reverse Recovery Time	t_{rr}			160		ns
Reverse Recovery Charge	Q_{rr}			0.98		μC
Reverse Recovery Energy	E_{rec}			0.14		mJ
Reverse Recovery Current	I_{rr}	V_R=400V, I_F=75A, di_F/dt=-440A/μs, T_J=125°C		17		A
Diode Reverse Recovery Time	t_{rr}			188		ns
Reverse Recovery Charge	Q_{rr}			2.97		μC
Reverse Recovery Energy	E_{rec}			0.47		mJ
Reverse Recovery Current	I_{rr}	V_R=400V, I_F=75A, di_F/dt=-440A/μs, T_J=150°C		20		A
Diode Reverse Recovery Time	t_{rr}			212		ns
Reverse Recovery Charge	Q_{rr}			3.26		μC
Reverse Recovery Energy	E_{rec}			0.54		mJ

Thermal characteristics

Parameter	Symbol	Min	Typ	Max	Units
Operating Junction Temperature Range	T_J	-40		175	°C
Storage Temperature Range	T_{stg}	-55		150	°C
Thermal Resistance from Junction to Case (IGBT)	Rth_{J-C}			0.35	°C/W
Thermal Resistance from Junction to Case (Diode)	Rth_{J-C}			0.45	°C/W
Thermal Resistance from Junction to Ambient	Rth_{J-A}			40	°C/W

Curve Characteristics

Fig. 1 - Typical Output Characteristic(T_j=25°C)

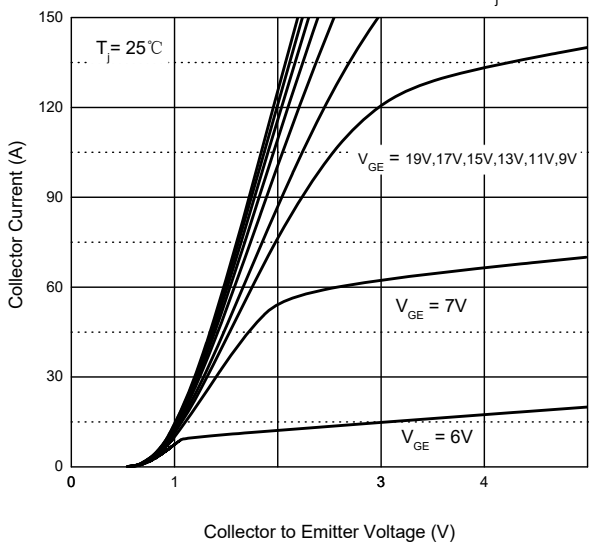


Fig. 2 - Typical Output Characteristic (T_j=150°C)

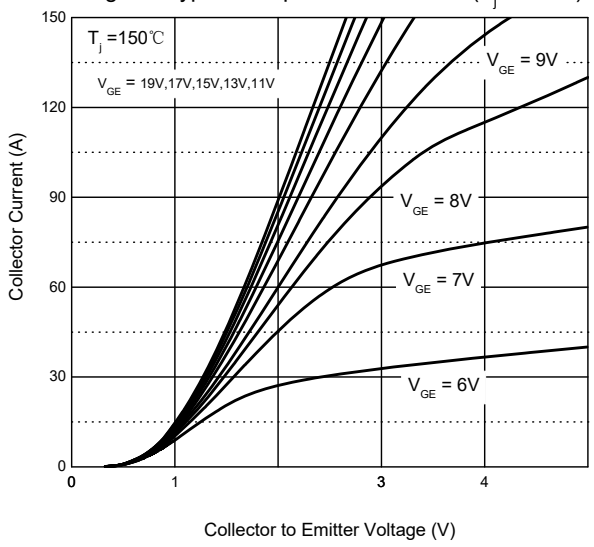


Fig. 3 - Typical Transfer Characteristic

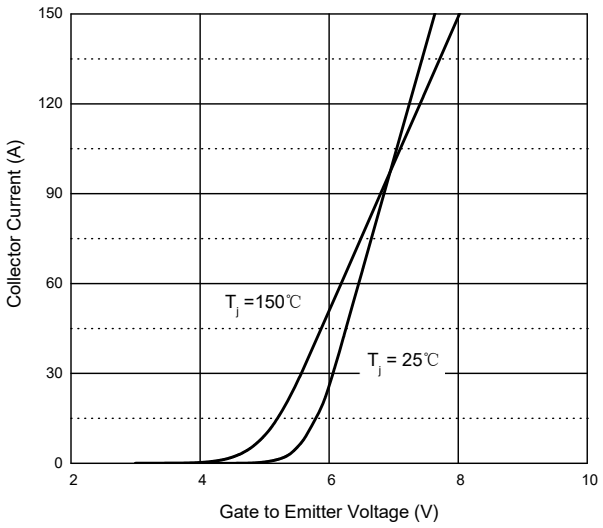


Fig. 4 - Diode Forward Current vs. Forward Voltage

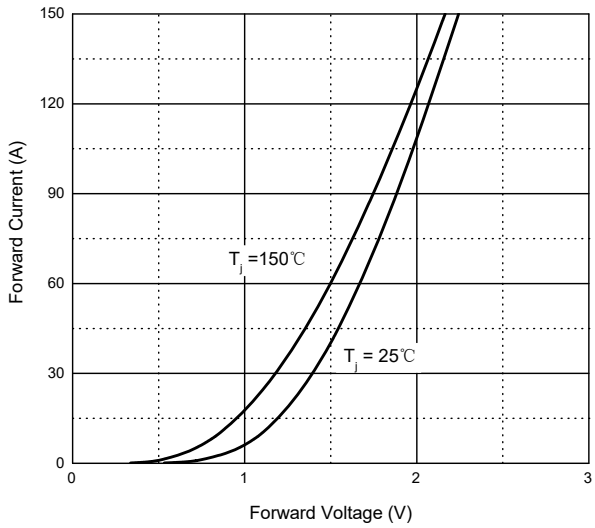


Fig. 5 - Diode VF vs. Junction Temperature

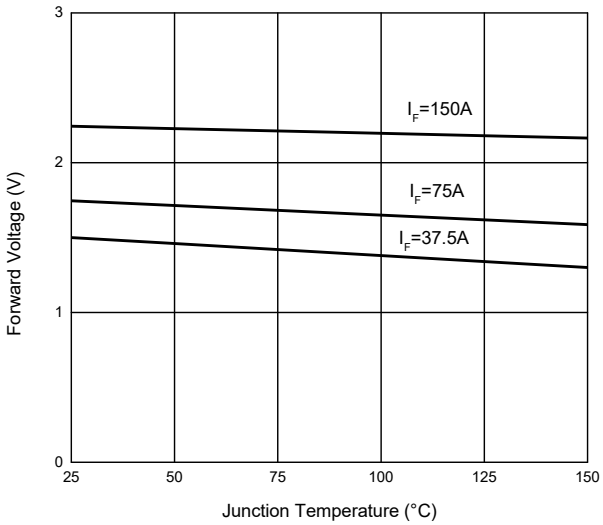
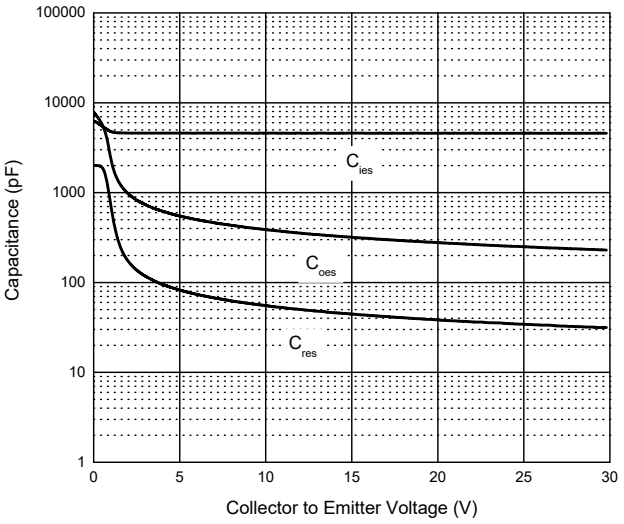


Fig. 6 - Capacitance Characteristics



Curve Characteristics

Fig. 7 - IGBT Switching Loss vs. IC

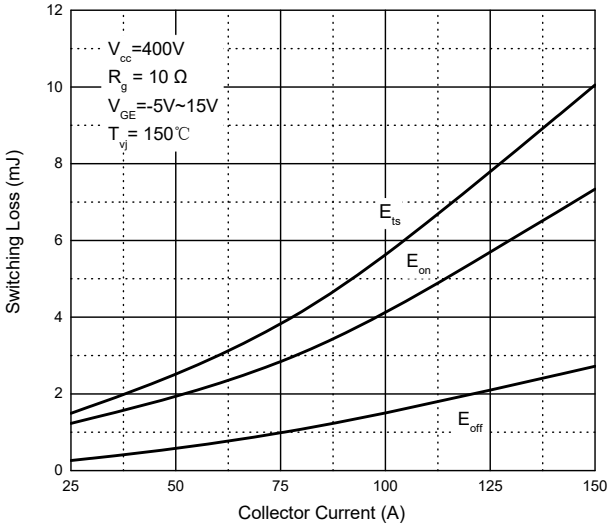


Fig. 8- IGBT Switching Loss vs. R_g

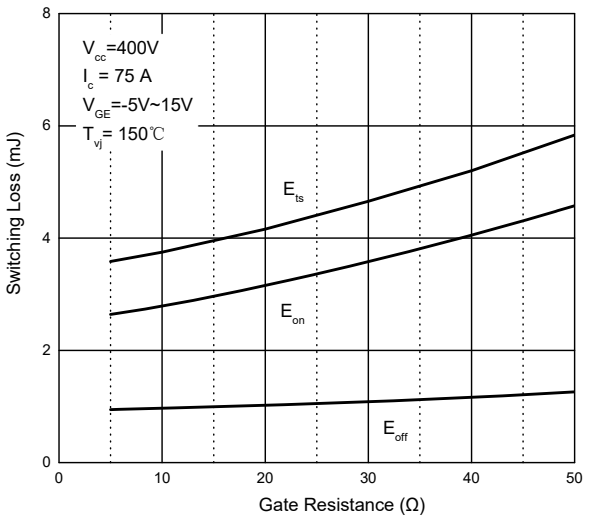


Fig. 9 -IGBT Switching Loss vs. Junction Temperature

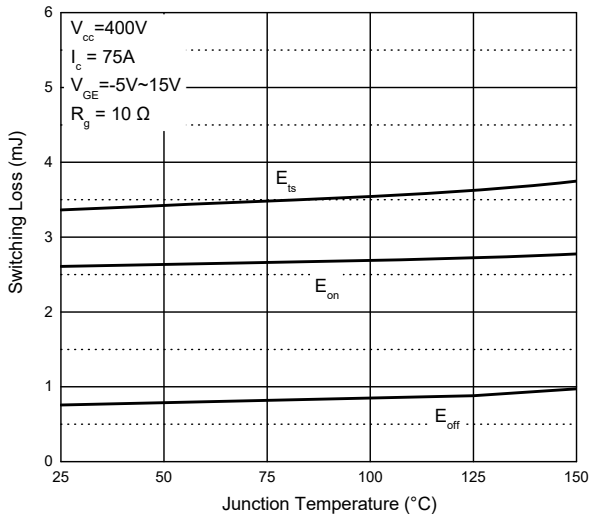


Fig. 10 - Switching Loss vs. VCE

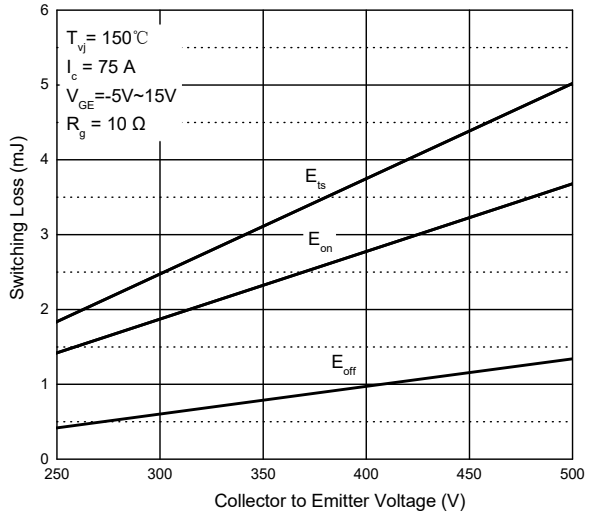


Fig. 11 - $V_{CE(sat)}$ vs. Junction Temperature

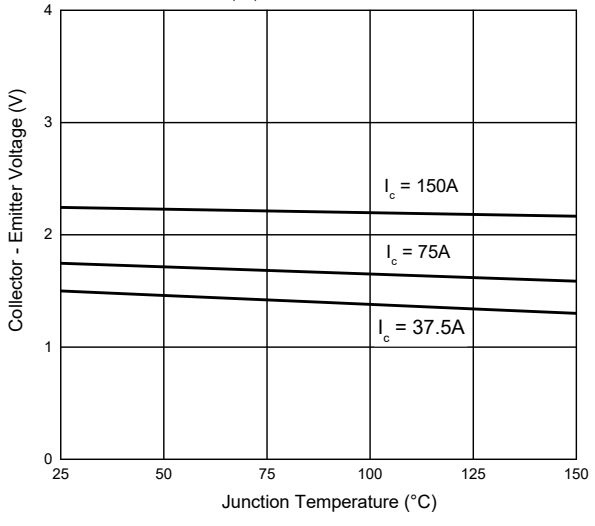
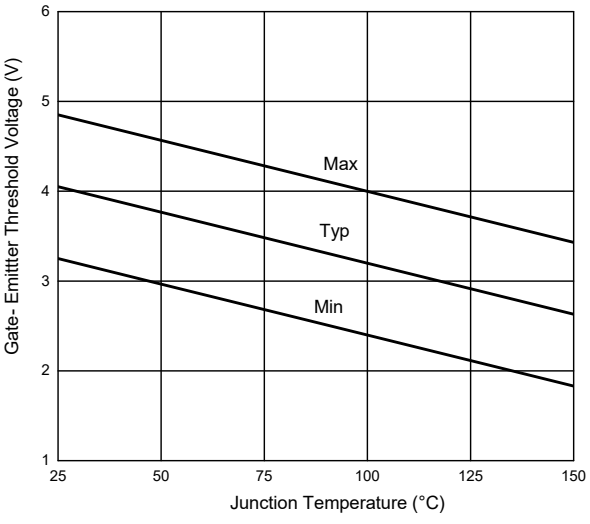


Fig. 12 $V_{GE(th)}$ vs. Junction Temperature



Curve Characteristics

Fig. 13 - Switching Time vs. Collect Current

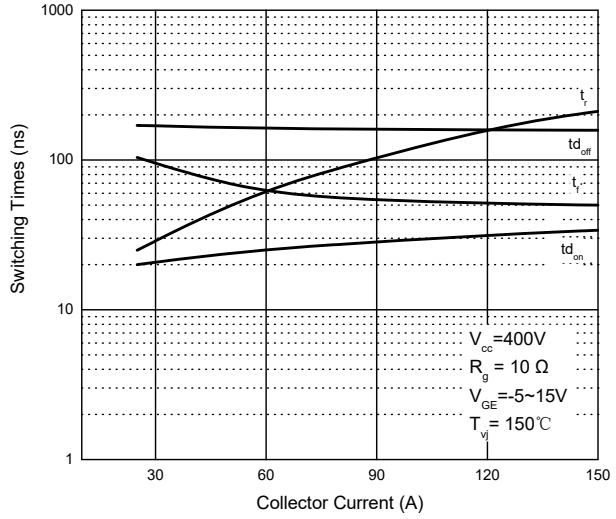


Fig. 14 - Switching Time vs. Gate Resistance

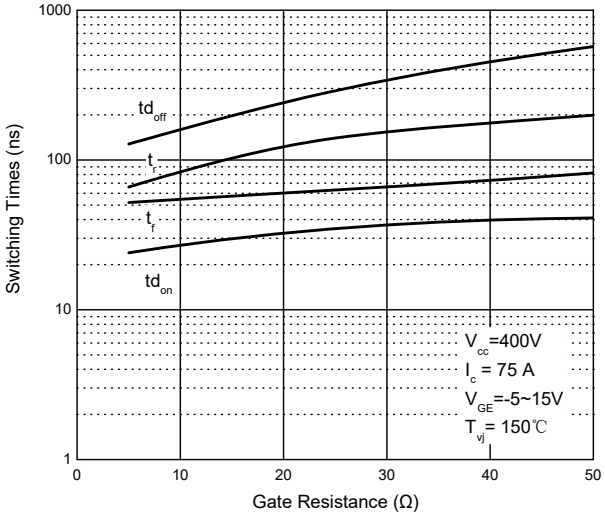


Fig. 15 - IGBT Transient Thermal Impedance

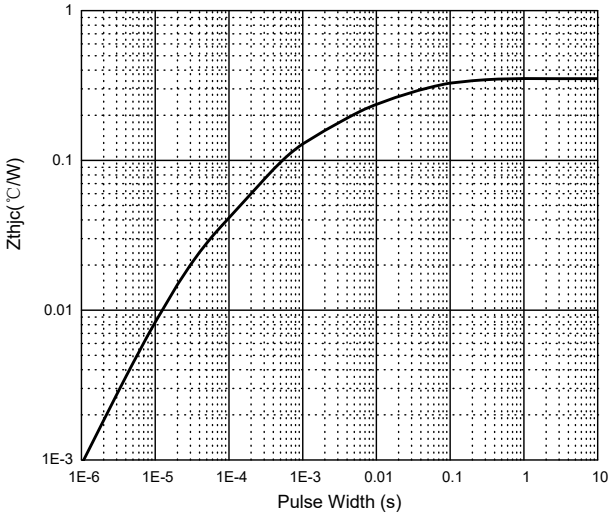


Fig. 16 - Diode Transient Thermal Impedance

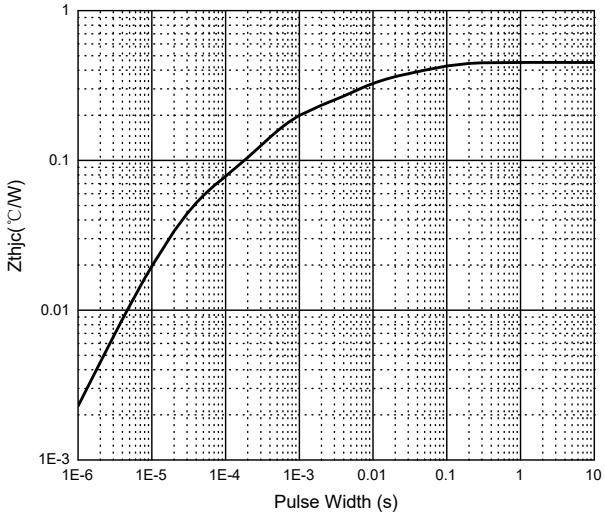


Fig. 17 - Collector Current vs. Case Temperature

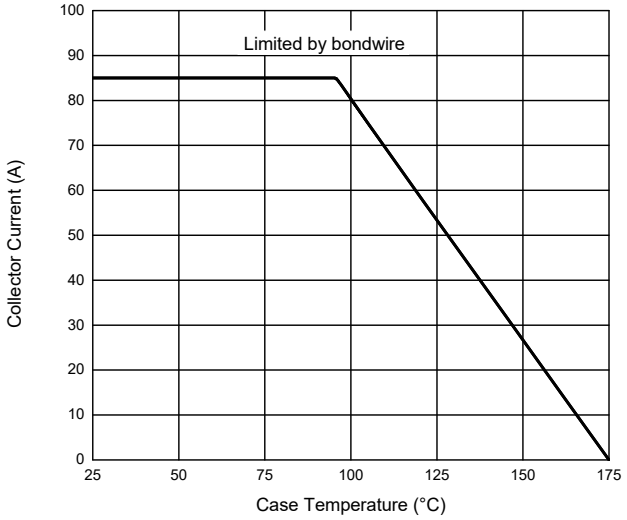
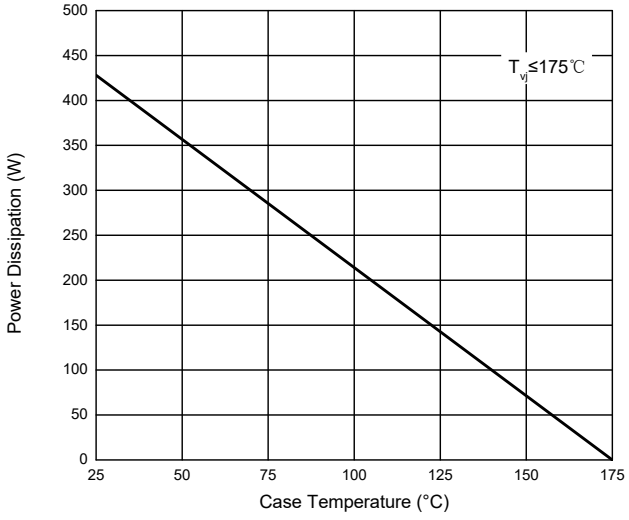
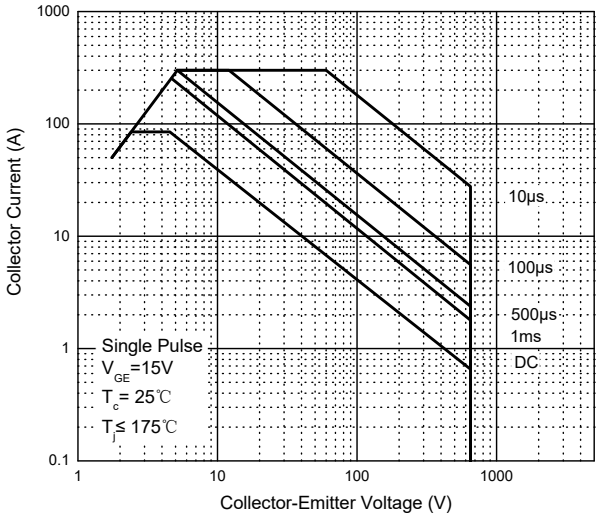


Fig. 18 - Power Derating



Curve Characteristics

Fig. 19 -FBSOA



Ordering Information

Device	Packing
MIZ75N65AH2Y-BP	Tube: 30pcs/Tube, 1800pcs/Ctn